

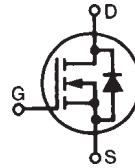
High Voltage Power MOSFET

IXTF1N250

$$\begin{aligned} V_{DSS} &= 2500V \\ I_{D25} &= 1A \\ R_{DS(on)} &\leq 40\Omega \end{aligned}$$

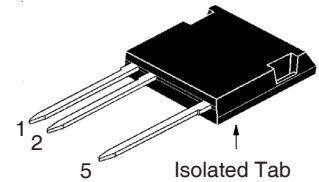
N-Channel Enhancement Mode

(Electrically Isolated Tab)



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	2500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	2500	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	1	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	6	A
P_D	$T_C = 25^\circ\text{C}$	110	W
T_J		- 55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		- 55 ... +150	$^\circ\text{C}$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ\text{C}$
T_{SOLD}	Plastic Body for 10s	260	$^\circ\text{C}$
M_d	Mounting Force	20..120 / 4.5..27	Nm/lb.in.
V_{ISOL}	50/60Hz, 1min	2500	V~
Weight		5	g

ISOPLUS i4-Pak™



1 = Gate
2 = Source
5 = Drain

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 2500V Electrical Isolation
- Molding Epoxies meet UL 94 V-0 Flammability Classification

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High Voltage Power Supplies
- Capacitor Discharge
- Pulse Circuits

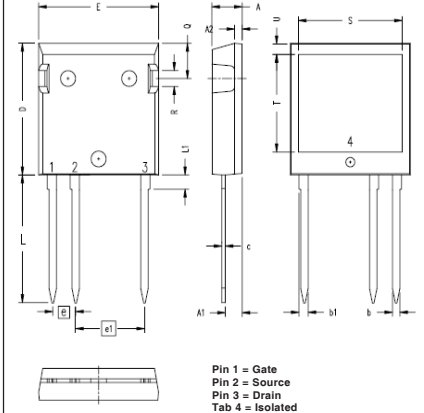
Symbol	Test Conditions	Characteristic Values	
	($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Min.	Typ.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu\text{A}$	2500	
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2.0	4.0
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$		± 100 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$, $V_{GS} = 0V$ Note 2, $T_J = 125^\circ\text{C}$	25	25 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1		40 Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 50\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	1.0	1.8	mS
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		1660	pF
C_{oss}			77	pF
C_{rss}			23	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = I_{D25}$ $R_G = 5\Omega$ (External)		69	ns
t_r			25	ns
$t_{d(off)}$			132	ns
t_f			39	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 600\text{V}$, $I_D = 0.5 \cdot I_{D25}$		41	nC
Q_{gs}			8	nC
Q_{gd}			16	nC
R_{thJC}				1.13 $^\circ\text{C/W}$
R_{thCS}		0.21		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_s	$V_{GS} = 0\text{V}$			1.5 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			6 A
V_{SD}	$I_F = 1\text{A}$, $V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 1\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 200\text{V}$		2.5	μs

ISOPLUS i4-Pak™ (HV) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.102	.118	2.59	3.00
A2	.046	.085	1.17	2.16
b	.045	.055	1.14	1.40
b1	.058	.068	1.47	1.73
C	.020	.029	0.51	0.74
D	.819	.840	20.80	21.34
E	.770	.799	19.56	20.29
e	.150 BSC		3.81 BSC	
e1	.450 BSC		11.43 BSC	
L	.780	.840	19.81	21.34
L1	.083	.102	2.11	2.59
Q	.210	.244	5.33	6.20
R	.100	.180	2.54	4.57
S	.660	.690	16.76	17.53
T	.590	.620	14.99	15.75
U	.065	.080	1.65	2.03

- Notes
1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
 2. Device must be heatsunk for high-temp I_{DSS} measurement to avoid thermal runaway.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves The Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

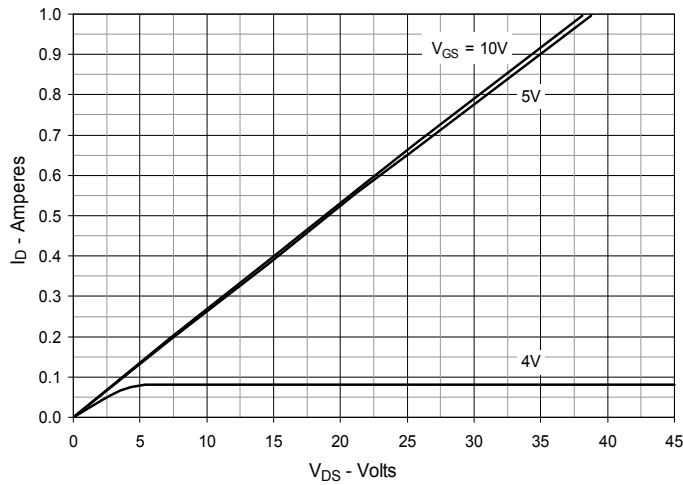
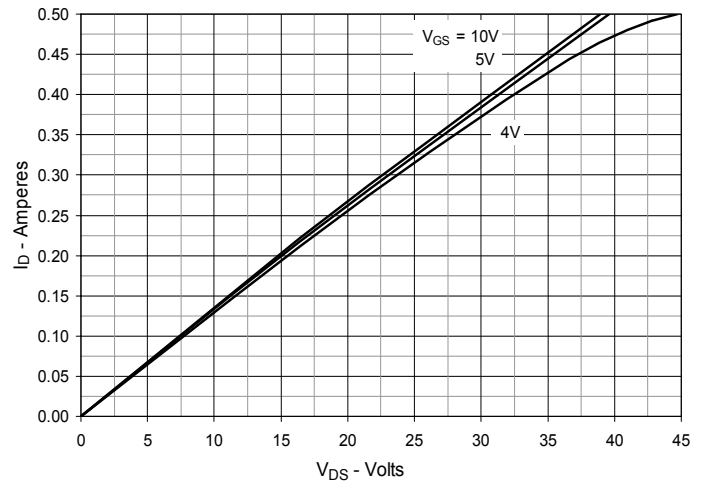
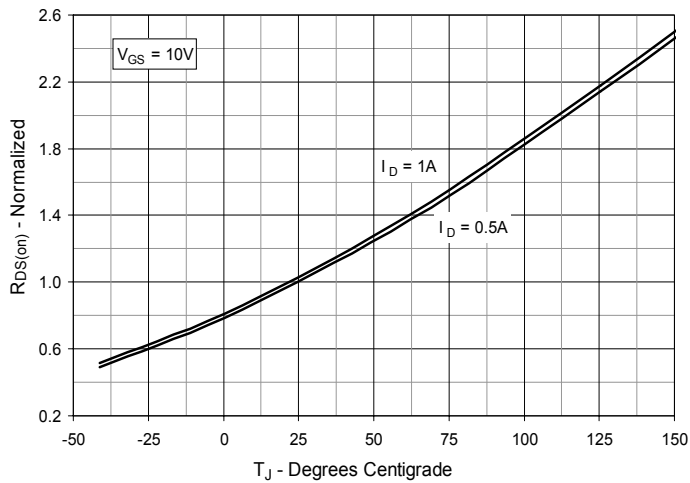
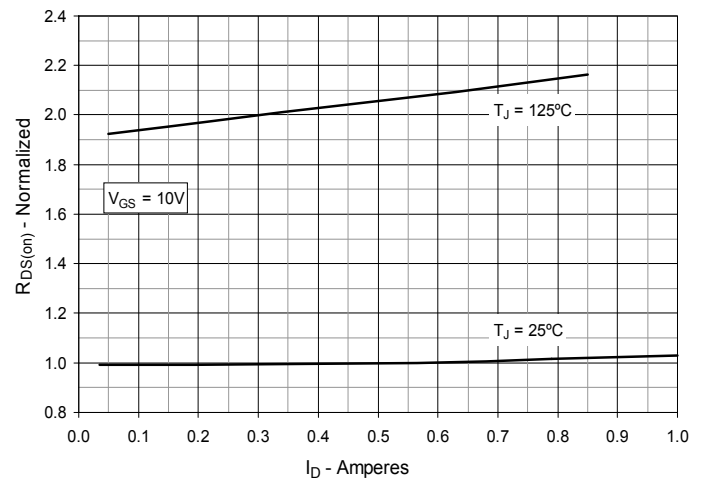
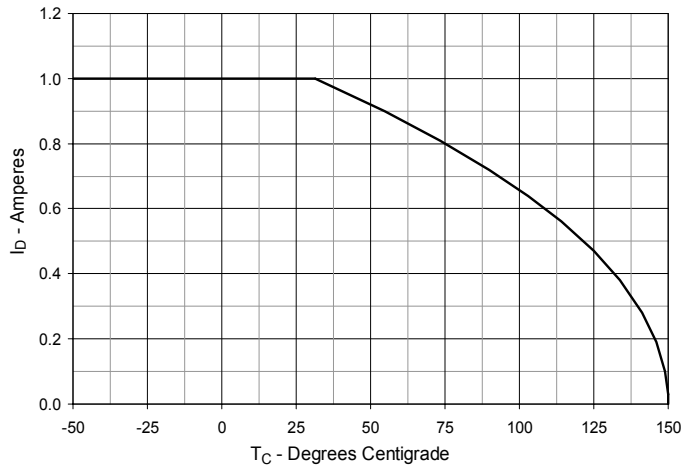
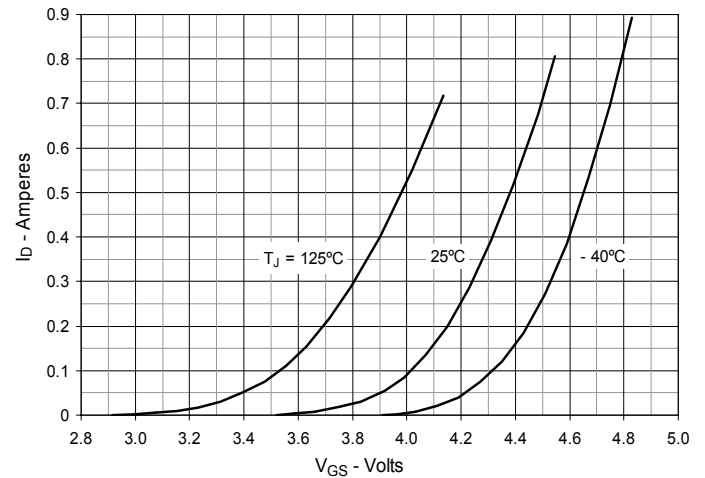
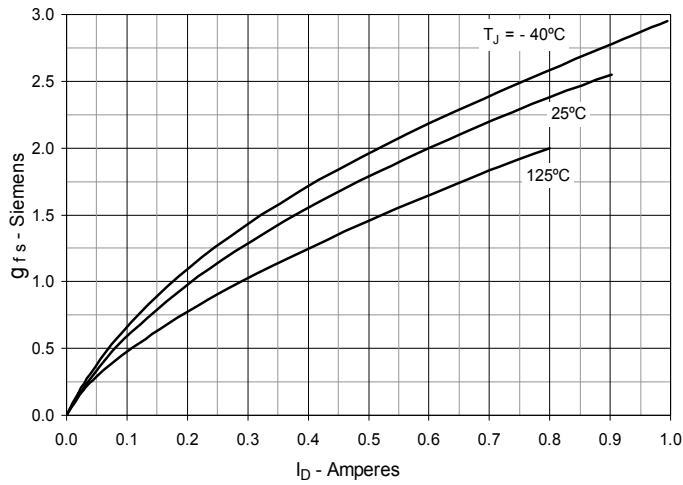
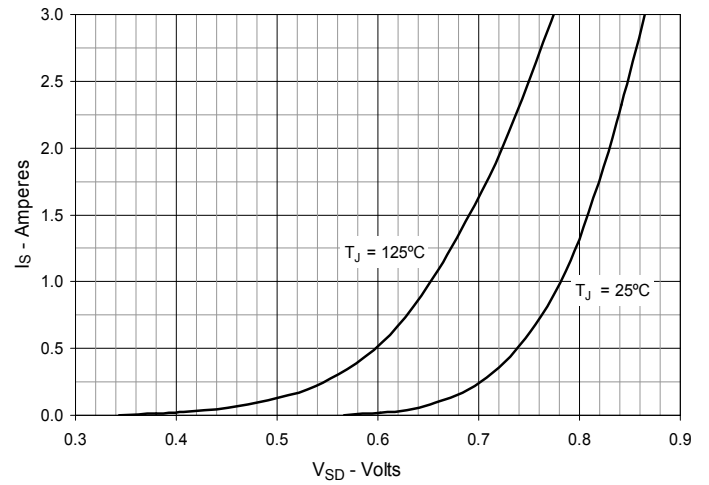
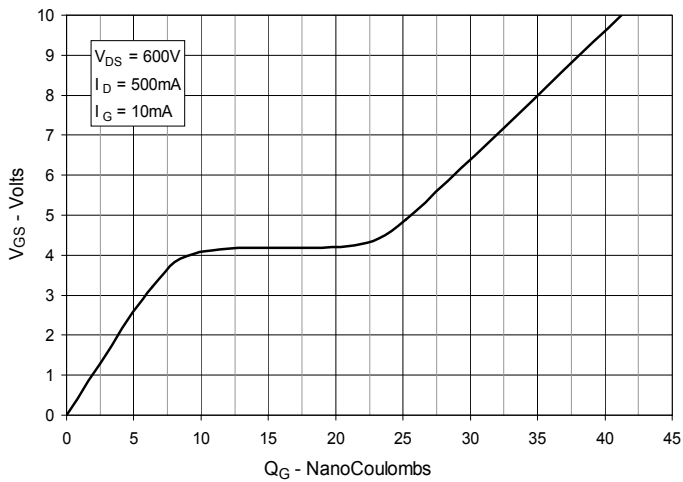
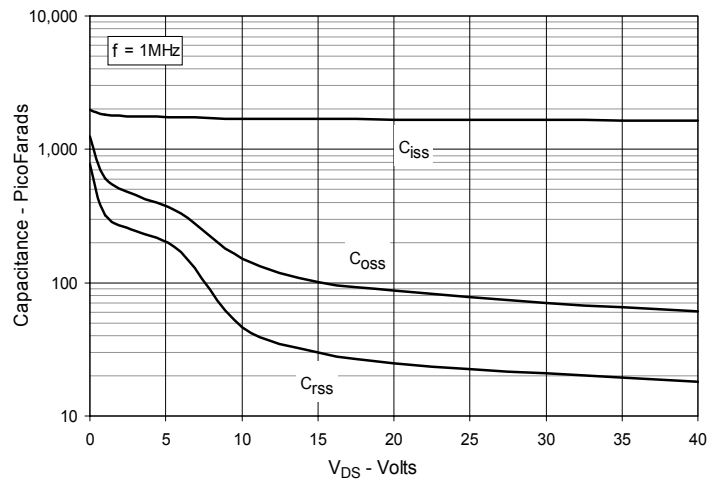
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 0.5\text{A}$ Value vs. Junction Temperature

Fig. 3. $R_{DS(on)}$ Normalized to $I_D = 0.5\text{A}$ Value vs. Drain Current

Fig. 5. Maximum Drain Current vs. Case Temperature

Fig. 6. Input Admittance


Fig. 7. Transconductance

Fig. 8. Forward Voltage Drop of Intrinsic Diode

Fig. 9. Gate Charge

Fig. 10. Capacitance

Fig. 11. Maximum Transient Thermal Impedance
